Vishay Semiconductors

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Hyperfast Rectifier, 75 A FRED Pt[®] G5



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACT	ERISTICS
I _{F(AV)}	75 A
V _R	600 V
V _F at I _F at 125 °C	1.4 V
t _{rr} (typ.)	29
I _{FSM}	565
T _J max.	175 °C
Package	TO-247AD 2L
Circuit configuration	Single

FEATURES

- Hyperfast and optimized Qrr
- Best in class forward voltage drop and switching losses trade off
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- AEC-Q101 qualified meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for soft switched and resonant converters, as well as medium frequency hard switching converters. This device is specifically designed to improve efficiency of high speed LLC output rectification stages of EV / HEV on-board battery chargers

MECHANICAL DATA

Case: TO-247AD 2L

Molding compound meets UL 94 V-0 flammability rating **Terminal:** matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V _{RRM}		600	V						
Average rectified forward current	I _{F(AV)}	T _C = 103 °C, D = 0.50	75							
Non-repetitive peak surge current	I _{FSM}	T_{C} = 25 °C, t_{p} = 10 ms, sine wave	565	A						
Repetitive peak forward current	I _{FRM}	T _C = 103 °C, D = 0.50, f = 20 kHz	150							
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C						

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	600	-	-				
Forward voltage	VF	I _F = 75 A	-	1.6	2.2	V			
Forward voltage	٧F	I _F = 75 A, T _J = 125 °C	-	1.4	-				
Reverse leakage current		$V_{R} = V_{R}$ rated	-	-	25				
neverse leakage current	IR	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA			
Junction capacitance	CT	V _R = 200 V	-	96	-	pF			
Series inductance	Ls	Measured to lead 5 mm from package body	-	8	-	nH			



RoHS COMPLIANT HALOGEN FREE



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 $^{\circ}$ C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS				
		$I_F = 1.0 \text{ A}, \text{ d}_F/\text{d}t = 100$) Α/μs, V _R = 30 V	-	29	-				
Reverse recovery time	t _{rr}	T _J = 25 °C		-	44	-	ns			
		T _J = 125 °C		-	69	-				
Peak recovery current		T _J = 25 °C	I _F = 50 A dI _F /dt = 1000 A/μs V _B = 400 V	-	18	-	A			
Feak recovery current	I _{RRM}	T _J = 125 °C		-	42	-				
Reverse recovery charge	0	T _J = 25 °C		-	484	-	nC			
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	1731	-				
	+	T _J = 25 °C		-	48	-	ns			
Reverse recovery time	t _{rr}	T _J = 125 °C		-	75	-				
Deels receivers a urrent		T _J = 25 °C	$I_{\rm F} = 75 {\rm A}$	-	21	-	A			
Peak recovery current	I _{RRM}	T _J = 125 °C	dl _F /dt = 1000 A/µs V _B = 400 V	-	46	-				
	0	T _J = 25 °C] ``	-	573	-	nC			
Reverse recovery charge	Q _{rr}	T _J = 125 °C]	-	2048	-				

THERMAL - MECHANICAL SPECIFICATIONS											
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS					
Thermal resistance, junction-to-case	R _{thJC}		-	-	0.5	°C/W					
Weight			-	5.5	-	g					
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)					
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C					
Marking device		Case style: TO-247AD 2L	E5PX7506LH								

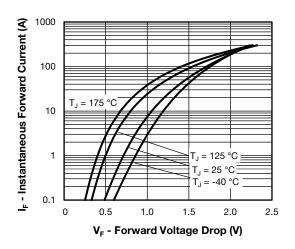


Fig. 1 - Forward Voltage Drop Characteristics

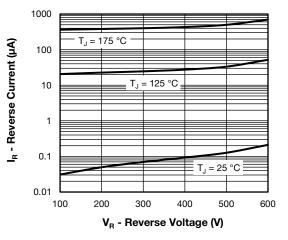


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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VS-E5PX7506LHN3

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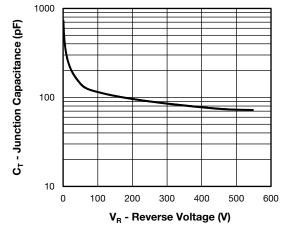


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

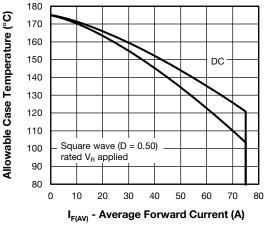


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

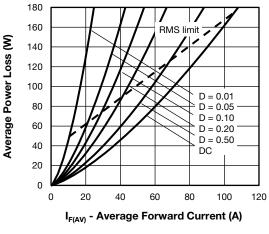


Fig. 5 - Forward Power Loss Characteristics

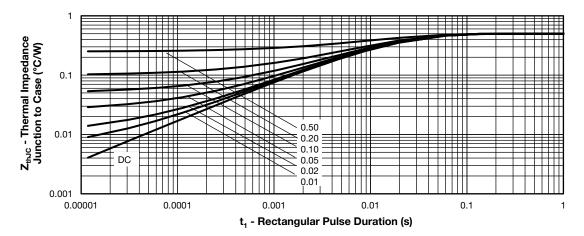


Fig. 6 - Transient Thermal Impedance, Junction to Case

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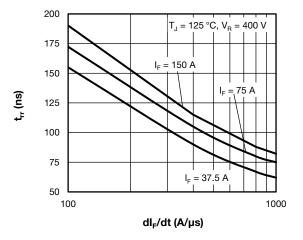


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

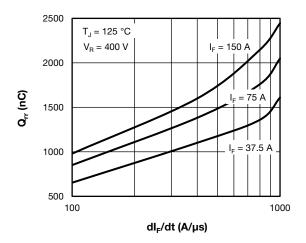


Fig. 8 - Typical Reverse Recovery Charge vs. dl_F/dt

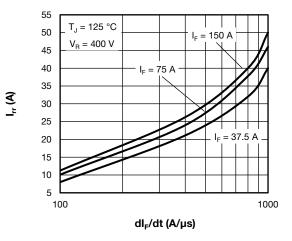


Fig. 9 - Typical Reverse Recovery Current vs. dl_F/dt



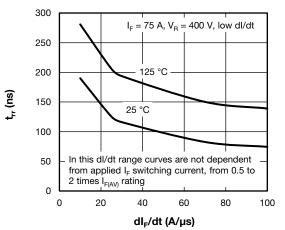
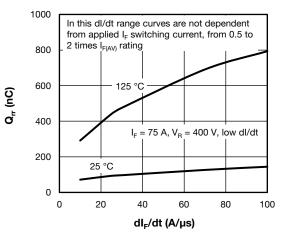


Fig. 10 - Typical Reverse Recovery Time vs. dl_F/dt





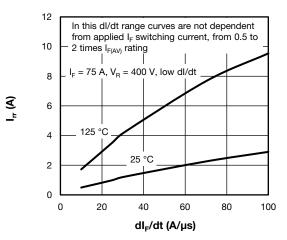


Fig. 12 - Typical Reverse Recovery Current vs. dl_F/dt

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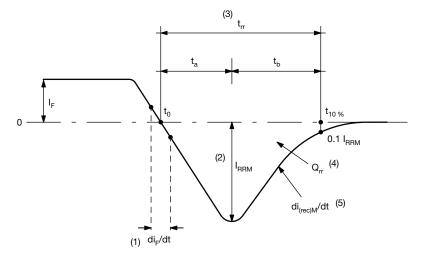


Fig. 13 - Reverse Recovery Waveform and Definitions

Notes

- $^{(1)}$ di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from t_0 , crossing point of negative going I_F, to point $t_{10\%}$, 0.1 I_{RRM}
- $^{(4)}~~Q_{rr}$ area under curve defined by t_0 and $t_{10~\%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t) dt$$

 $^{(5)}$ di_(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}



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ORDERING INFORMATION TABLE

Device code	VS-	E	5	Р	x	75	06	L	н	N3		
	1	2	3	4	5	6	(7)	8	9	10		
	1 .	· Visł	nay Sem	niconduo	ctors pro	oduct						
	2 -											
	3.	- FRED Pt [®] Gen 5										
	4	- P=	TO-247	' packag	je							
	5		Process type: X = hyperfast recovery									
	6 -	- Cur	rent rati	ng (75 =	= 75 A)							
	7 -	· Volt	age rati	ng (06 =	= 600 V)							
	8 -	8 - Package: L = long lead (TO-247AD)										
	9 -	- H = AEC-Q101 qualified										
	10			ntal digit en-free,		complia	nt, and	totally l	ead (Pb)-free		

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-E5PX7506LHN3	25	500	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95536			
Part marking information	www.vishay.com/doc?95648			



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TO-247AD 2L

DIMENSIONS in millimeters and inches



Section C - C, D - D

(b, b2)

(4)

View	<u>/ B</u>

SYMBOL	MILLIN	IETERS	INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES	
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES		STMDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209			E	15.29	15.87	0.602	0.625	3
A1	2.21	2.59	0.087	0.102			E1	13.46	-	0.53	-	
A2	1.50	2.49	0.059	0.098			е	5.46	BSC	0.215	5 BSC	
b	0.99	1.40	0.039	0.055			ØК	0.2	254	0.0	010	
b1	0.99	1.35	0.039	0.053			L	19.81	20.32	0.780	0.800	
b2	1.65	2.39	0.065	0.094			L1	3.71	4.29	0.146	0.169	
b3	1.65	2.34	0.065	0.092			ØР	3.56	3.66	0.14	0.144	
С	0.38	0.89	0.015	0.035			Ø P1	-	6.98	-	0.275	
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	' BSC	
D2	0.51	1.35	0.020	0.053				•		•		•

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

(5) Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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